



MMBTA94

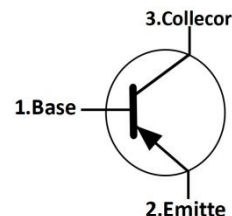
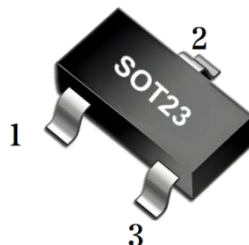
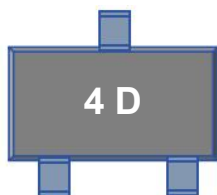
PNP SILICON TRANSISTOR

FEATURES

- * High Breakdown Voltage

MARKING

Type Code: Marking: 4 D



ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

SYMBOL	PARAMETER	VALUE	UNIT
BV _{CB0}	Collector-base voltage	-400	V
BV _{CEO}	Collector-emitter voltage	-400	V
BV _{EB0}	Emitter-base voltage	-5	V
I _C	Collector current	-200	mA
I _{CM}	Collector Current -Pulsed	-300	mA
P _C	Collector Power Dissipation	350	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-60~150	°C
R _{θJA}	Thermal Resistance From Junction To Ambient	357	°C/W

ELECTRICAL CHARACTERISTICS (TJ=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CB0}	I _C =-100μA, I _E =0	-400		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-400		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5		V
Collector cutoff current	I _{CB0}	V _{CB} =-400V, I _E =0		-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-400V, I _B =0		-5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0		-0.1	μA
DC Current Gain	h _{FE1}	V _{CE} =-10V, I _C =-10mA	80	300	
	h _{FE2}	V _{CE} =-10V, I _C =-1mA	70		
	H _{FE3}	V _{CE} =-10V, I _C =-100mA	40		
	h _{FE4}	V _{CE} =-10V, I _C =-50mA	40		

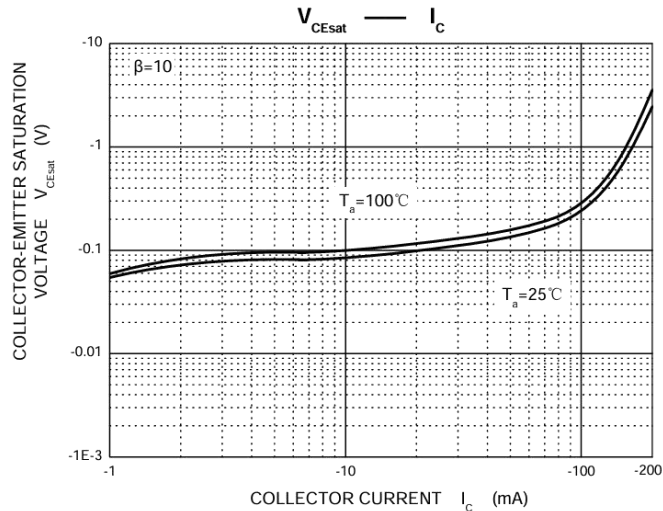
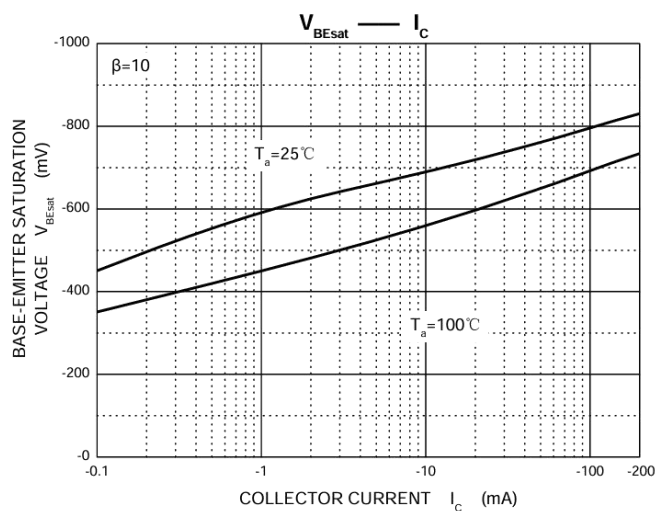
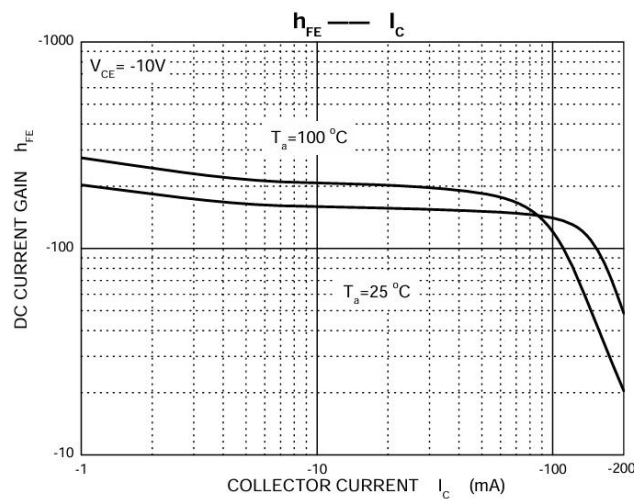
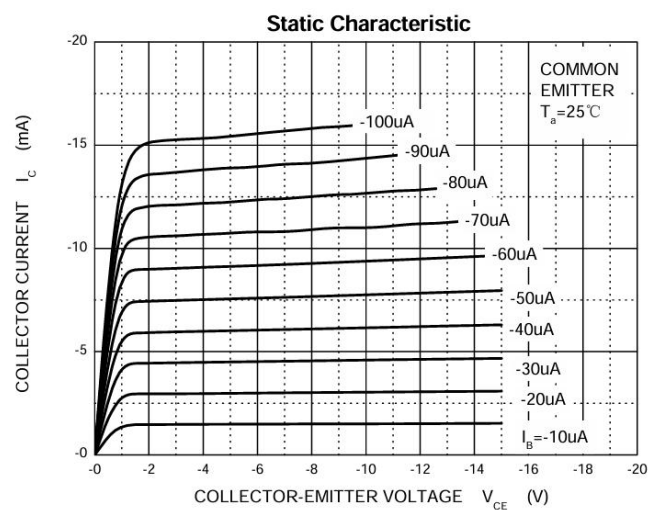


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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$		-0.2	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$		-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$		-0.75	V
Transition frequency	f_T	$V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 30\text{MHz}$	50		MHz

TYPICAL CHARACTERISTICS

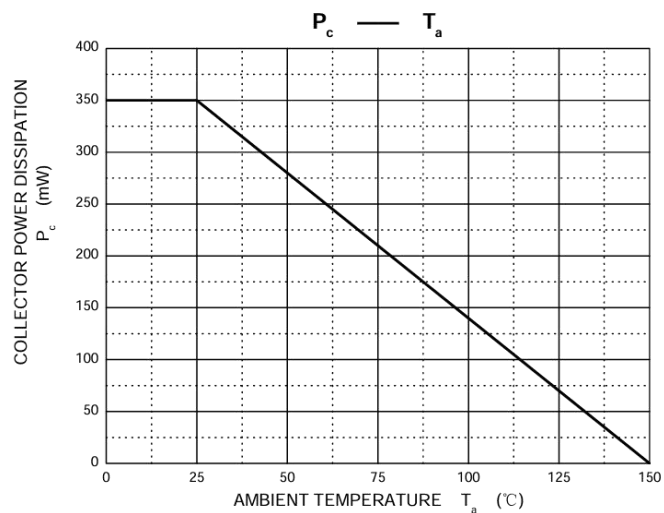
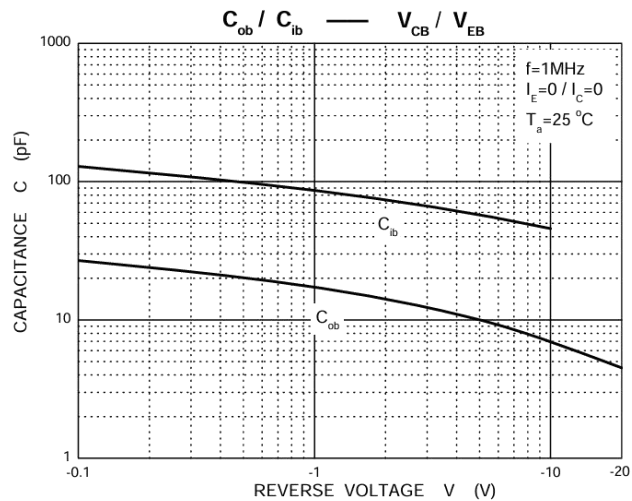
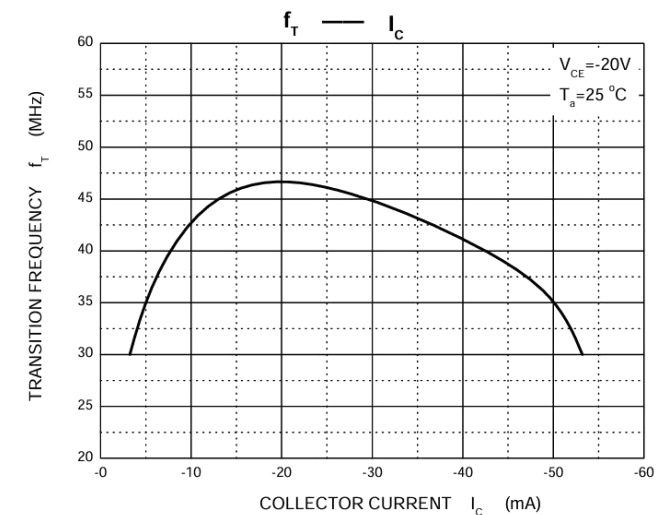




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■ TYPICAL CHARACTERISTICS(Con.t)

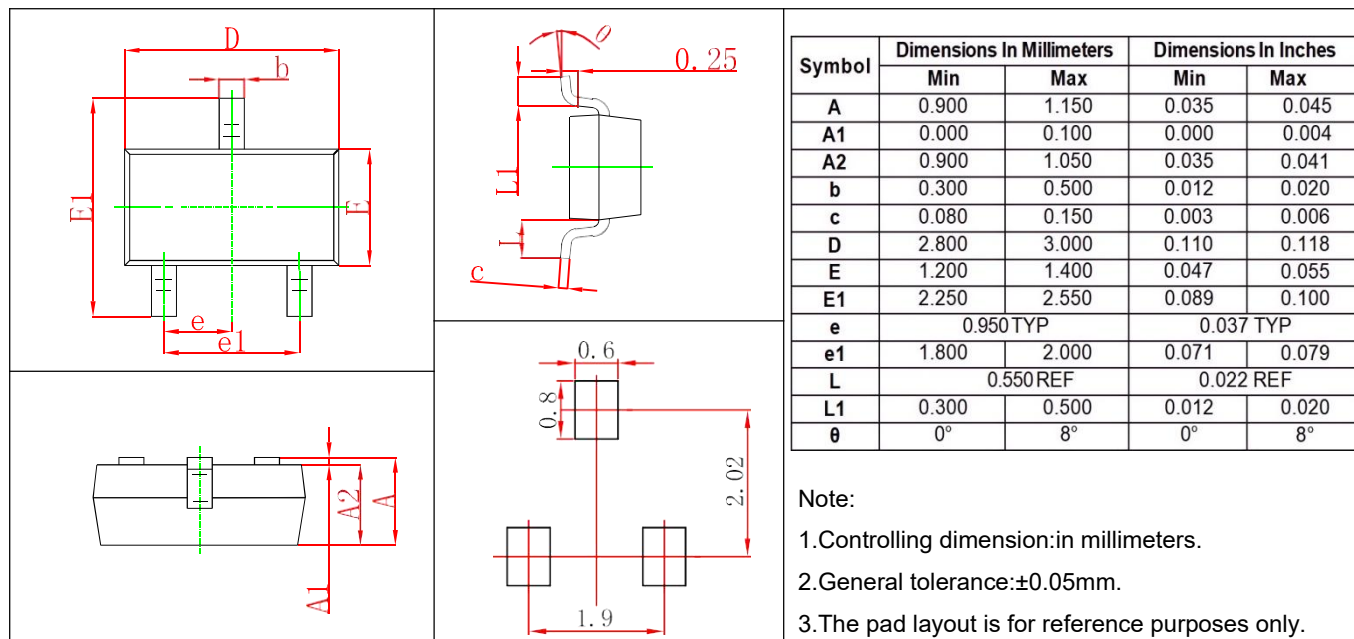




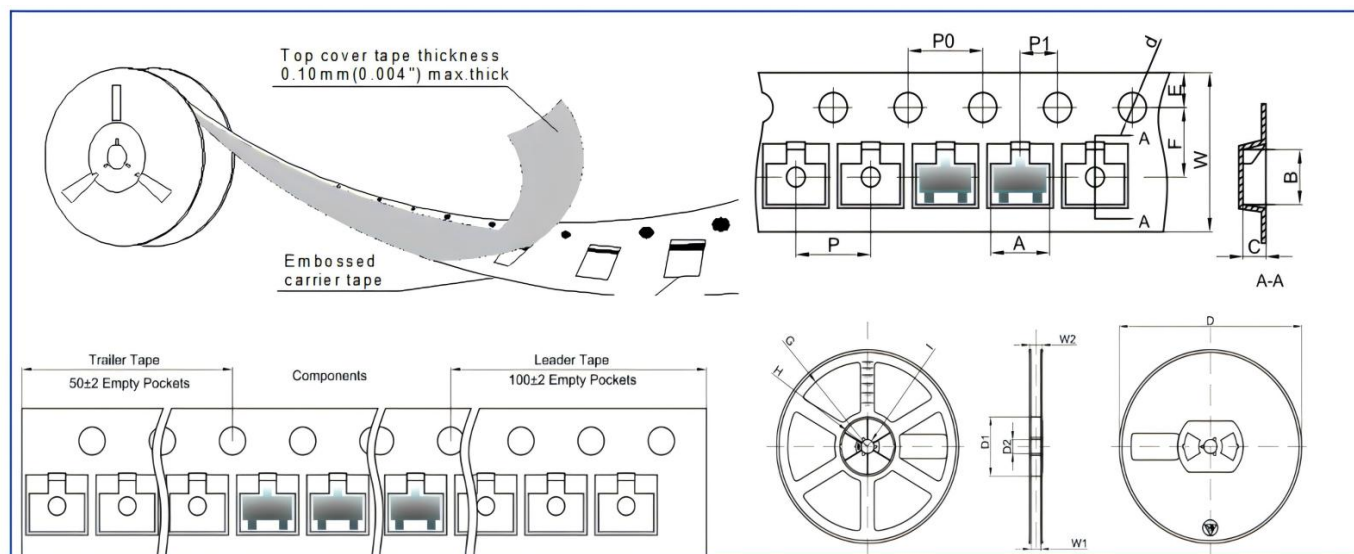
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PNP SILICON TRANSISTOR

SOT23 PACKAGE OUTLINE DIMENSIONS



REEL PACKING



Dimensions are in millimeter

PKG TYPE	A	B	C	d	E	F	Po	P	P1	W
SOT-23	3.15	2.77	1.22	Φ1.50	1.75	3.50	4.00	4.00	2.00	8.00
Reel Option	D	D1	D2	G	H	I	W1	W2	Q.TY PER REEL	
7" Dia	Φ178.0	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30	3000PCS	
13" Dia	φ330.0	/	13.00	/	/	R6.50	9.50	12.30	10000PCS	